N-Channel Enhancement Mode Power MOSFET

Features

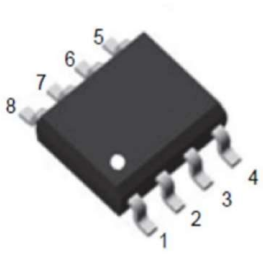
- VDS= 150V, ID= 5.2A
  RDS(ON) < 31 mΩ @ VGS = 10V
  RDS(ON) < 40 mΩ @ VGS =4.5V

General Features

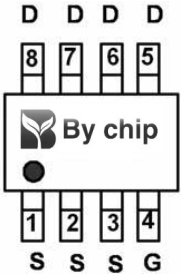
- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- Lead Free and Green Available

100% UIS TESTED!
100% ΔVds TESTED!

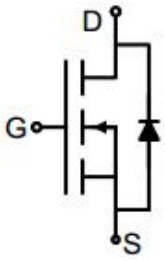
RoHS



SOP-8



pin assignment



Schematic diagram

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	ymbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	
Gate-Source Voltage	V_{GS}	±20	
Drain Current-Continuous	I_D	5.2	
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	3.	A
Pulsed Drain Current(Note 1)	I_{DM}	42	
Maximum Power Dissipation	P_D	3.5	
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient Note 2)	$R_{\theta JA}$	35.7	℃

Electrical Characteristics (T_A=25℃unless otherwise noted)

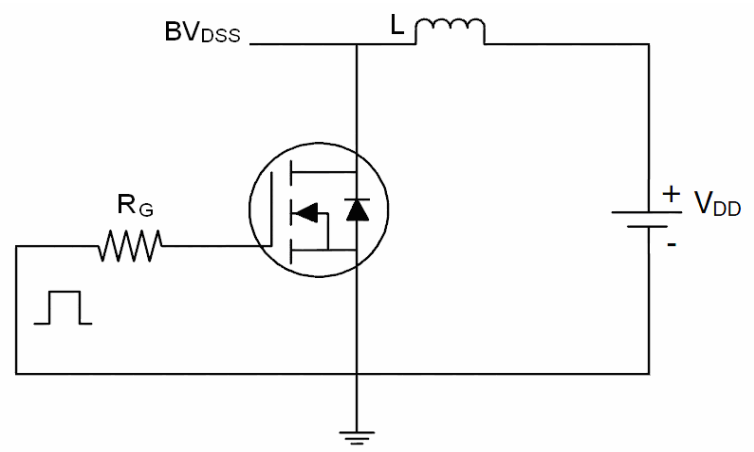
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	150		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=150V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.5		4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5.2A	-		31	mΩ
Forward Transconductance	g_{FS}	V_{DS}=50V,I_D=5.2A	12	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=25V,V_{GS}=0V, F=1.0MHz	-	1700	-	PF
Output Capacitance	C_{oss}		-	190	-	PF
Reverse Transfer Capacitance	C_{rss}		-	90	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=75V,I_D=3.1A V_{GS}=10V,R_{GEN}=6.5Ω	-	15	-	nS
Turn-on Rise Time	t_r		-	13	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	26	-	nS
Turn-Off Fall Time	t_f		-	14	-	nS
Total Gate Charge	Q_g	V_{DS}=75V,I_D=3.1A, V_{GS}=10V	-	35.8	-	nC
Gate-Source Charge	Q_{gs}		-	7.5	-	nC
Gate-Drain Charge	Q_{gd}		-	13	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=3.1A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	2.7	A
Reverse Recovery Time	trr	T_J = 25°C, I_F = 3.1A, di/dt = 100A/μs	-	50	-	nS
Reverse Recovery Charge	Qrr		-	140	-	nC

Notes:

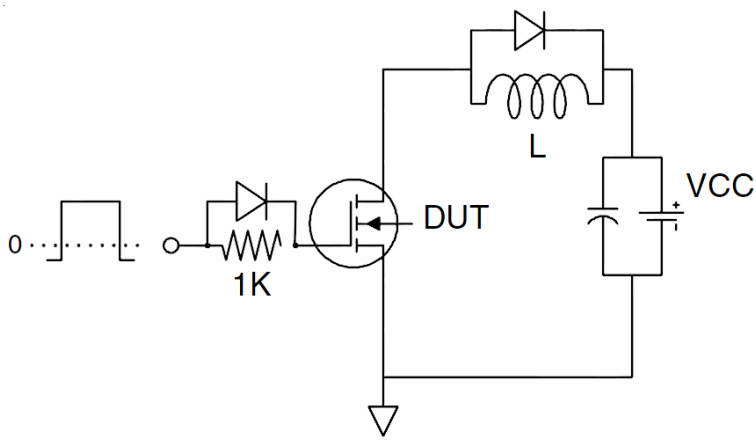
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production.

Test Circuit

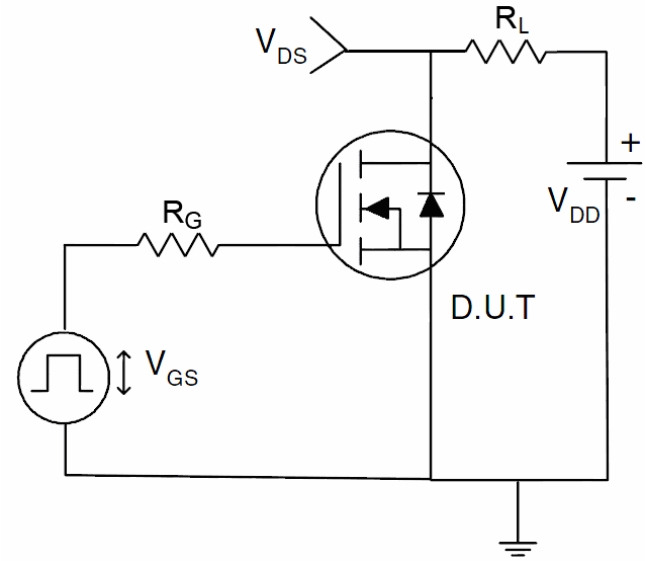
1) E_{AS} test Circuits



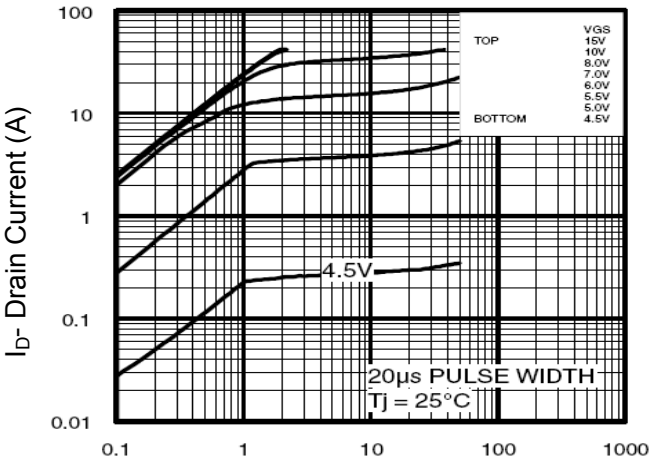
2) Gate charge test Circuit



3) Switch Time Test Circuit

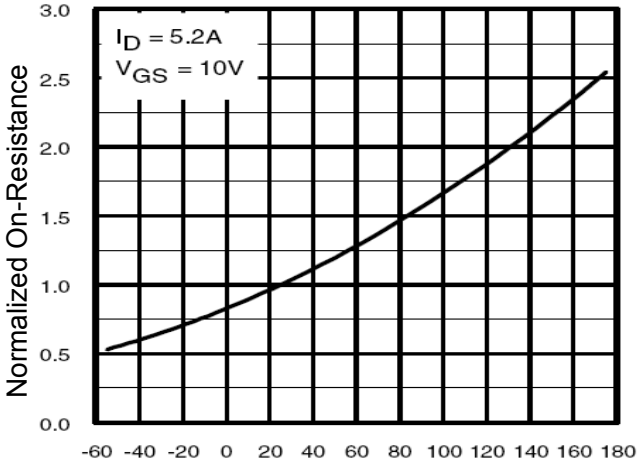


Typical Electrical and Thermal Characteristics (Curves)



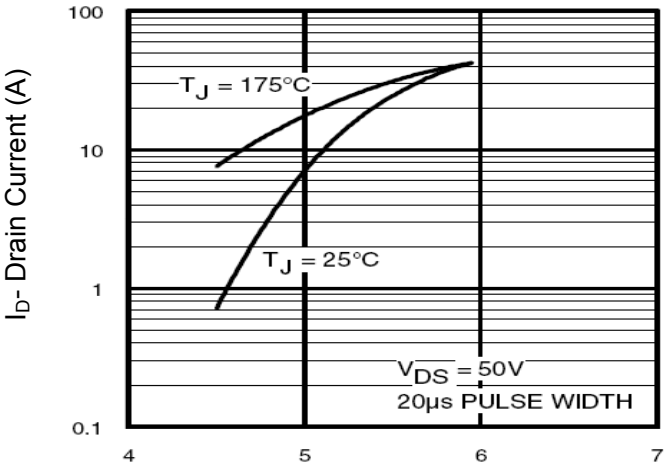
Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



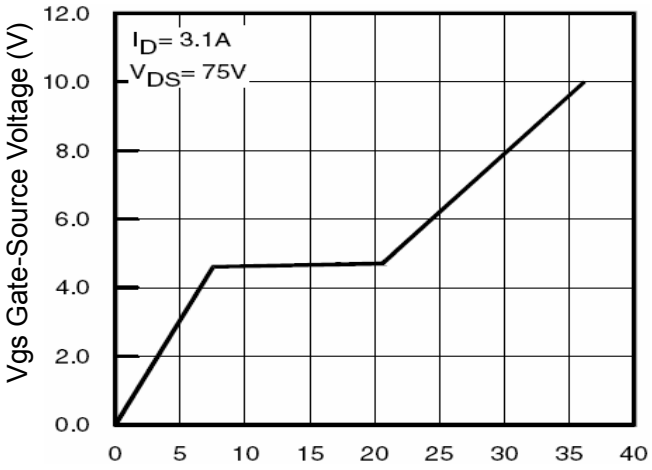
T_J-Junction Temperature(℃)

Figure 4 Rdson-JunctionTemperature



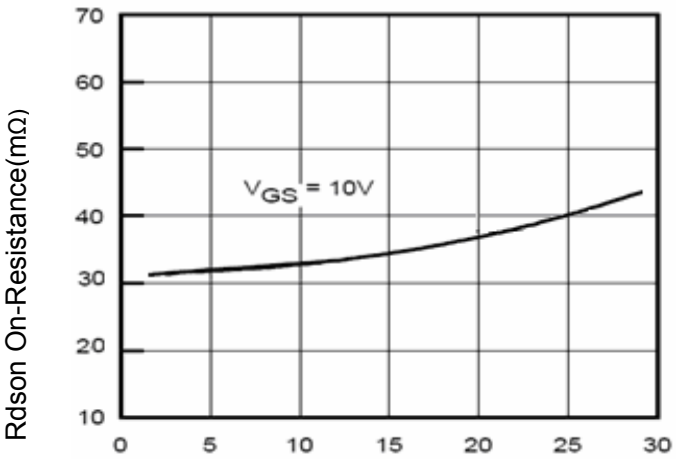
Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics



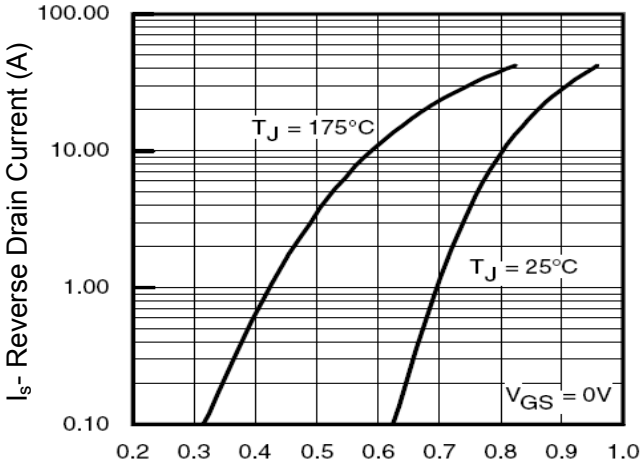
Qg Gate Charge (nC)

Figure 5 Gate Charge



I_D- Drain Current (A)

Figure 3 Rdson- Drain Current



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

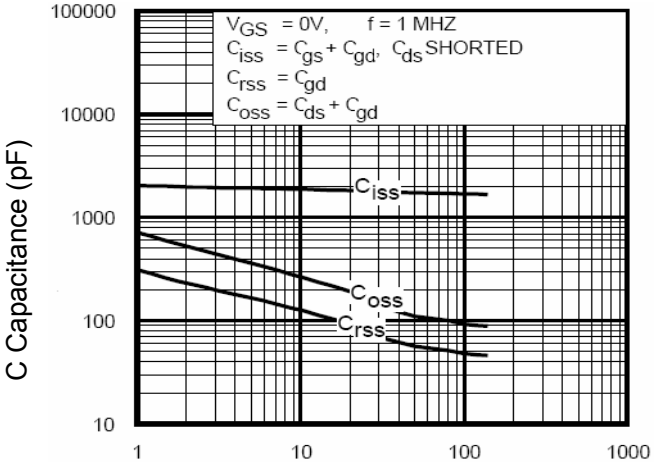


Figure 7 Capacitance vs Vds

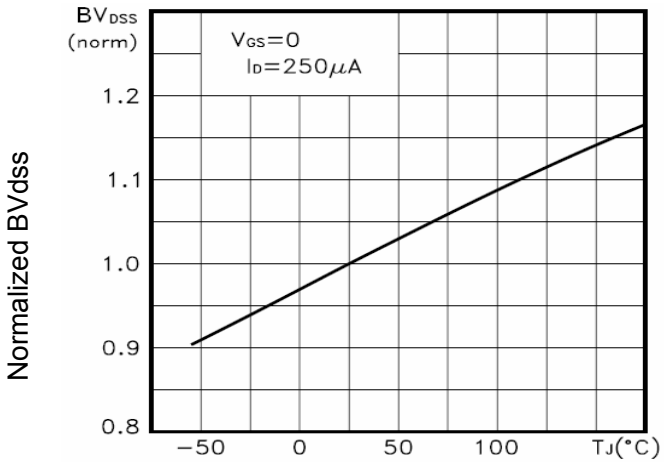


Figure 9 BV_{DSS} vs Junction Temperature

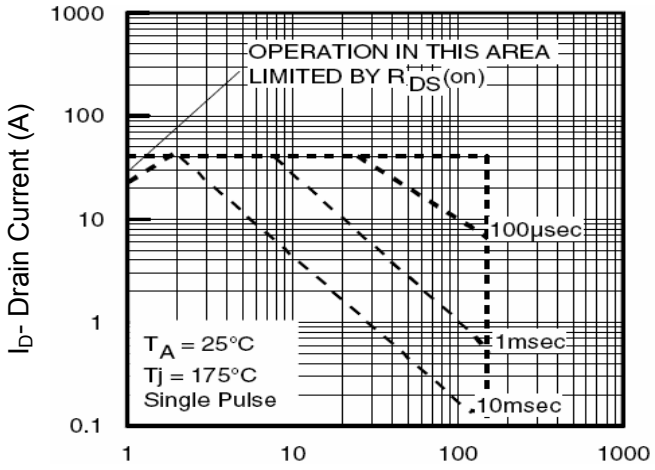


Figure 8 Safe Operation Area

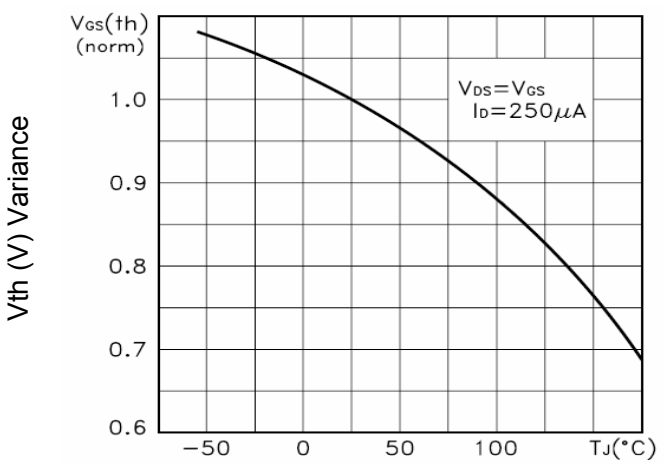


Figure 10 $V_{GS(th)}$ vs Junction Temperatur

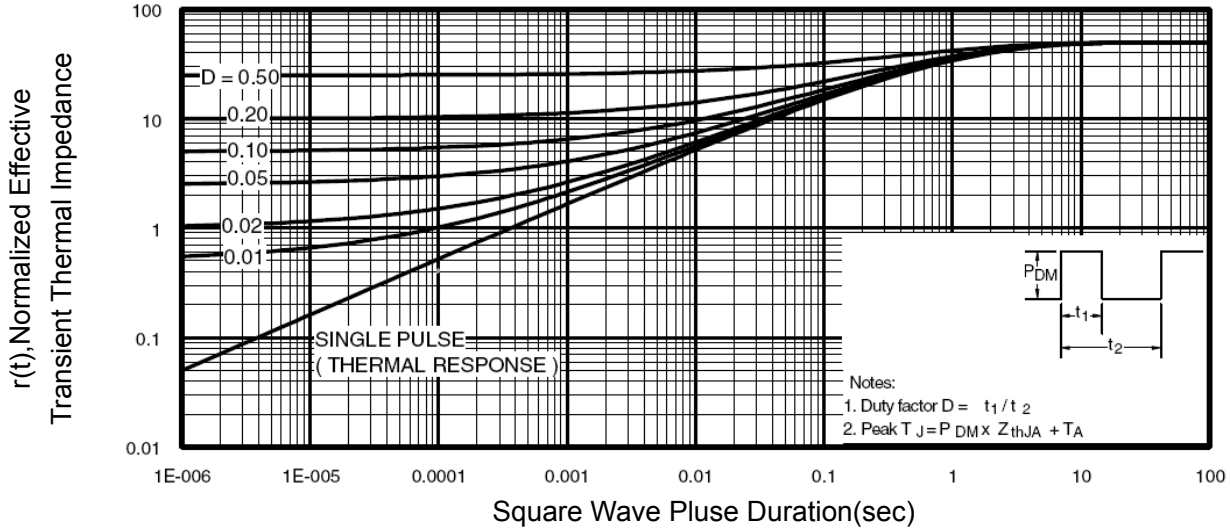


Figure 11 Normalized Maximum Transient Thermal Impedance